

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	64084	semiconductor and (trench or groove)	USPAT; EPO; JPO; Derwent; IBM TDB	2001/02/26 15:26
2	BRS	L2	8267	1 and gate and source and drain	USPAT; EPO; JPO; Derwent; IBM TDB	2001/02/26 15:27
3	BRS	L3	437	2 and channel and drift	USPAT; EPO; JPO; Derwent; IBM TDB	2001/02/26 15:28
4	BRS	L4	142	3 and center	USPAT; EPO; JPO; Derwent; IBM TDB	2001/02/26 15:29
5	BRS	L6	0	5 and (on adj resistance)	USPAT; EPO; JPO; Derwent; IBM TDB	2001/02/26 15:29
6	BRS	L5	88	4 and (bipolar or igt)	USPAT; EPO; JPO; Derwent; IBM TDB	2001/02/26 15:30

	Comments	Error Definition	Errors
1			0
2			0
3			0
4			0
5			0
6			0